Fei Zeng

List of Publications by Year in Descending Order

153 papers	6,865 citations	40 h-index	80 g-index
161 ext. papers	7,637 ext. citations	5.4 avg, IF	5.86 L-index

#	Paper	IF	Citations
153	SAW Filters With Excellent Temperature Stability and High Power Handling Using LiTaO3/SiC Bonded Wafers. *Journal of Microelectromechanical Systems*, **2022**, 1-8	2.5	2
152	Memristive Behaviors Dominated by Reversible Nucleation Dynamics of Phase-Change Nanoclusters.. *Small*, **2022**, e2105070	11	0
151	Systematical Study of the Basic Properties of Surface Acoustic Wave Devices Based on ZnO and GaN Multilayers. *Electronics (Switzerland)*, **2021**, 10, 23	2.6	8
150	Wideband and Low-Loss Surface Acoustic Wave Filter Based on 15°YX-LiNbO3/SiO2/Si Structure. *IEEE Electron Device Letters*, **2021**, 42, 438-441	4.4	21
149	Enhanced Coupling Coefficient in Dual-Mode ZnO/SiC Surface Acoustic Wave Devices with Partially Etched Piezoelectric Layer. *Applied Sciences (Switzerland)*, **2021**, 11, 6383	2.6	3
148	Target Controllability of Two-Layer Multiplex Networks Based on Network Flow Theory. *IEEE Transactions on Cybernetics*, **2021**, 51, 2699-2711	10.2	4
147	Optimal Target Control of Complex Networks With Selectable Inputs. *IEEE Transactions on Control of Network Systems*, **2021**, 8, 212-221	4	2
146	Near 30% fractional bandwidth surface acoustic wave filters with novel electrode configuration. *Progress in Natural Science: Materials International*, **2021**, 31, 852-852	3.6	1
145	Structure with thin SiO/SiN bilayer and Al electrodes for high-frequency, large-coupling, and low-cost surface acoustic wave devices. *Ultrasonics*, **2021**, 115, 106460	3.5	2
144	A Multilayered Structure for Packageless Acoustic- Wave Devices With Ultra-Small Sizes. *Journal of Microelectromechanical Systems*, **2021**, 30, 589-596	2.5	3
143	High-Performance Surface Acoustic Wave Devices Using LiNbO3/SiO2/SiC Multilayered Substrates. *IEEE Transactions on Microwave Theory and Techniques*, **2021**, 69, 3693-3705	4.1	10
142	Performance Improvement of Conductive Bridging Random Access Memory by Electrode Alloying. *Journal of Physical Chemistry C*, **2020**, 124, 11438-11443	3.8	6
141	Cluster-Type Filaments Induced by Doping in Low-Operation-Current Conductive Bridge Random Access Memory. *ACS Applied Materials & Interfaces*, **2020**, 12, 29481-29486	9.5	3
140	Adaptive Deformation of Ionic Domains in Hydrogel Enforcing Dielectric Coupling for Sensitive Response to Mechanical Stretching. *Advanced Intelligent Systems*, **2020**, 2, 2000016	6	
139	High-frequency and high-temperature stable surface acoustic wave devices on ZnO/SiO2/SiC structure. *Journal Physics D: Applied Physics*, **2020**, 53, 305102	3	6
138	Implementing a Type of Synaptic Coupling between Excitatory and Inhibitory Cells by Using Pt/Poly(3,4-ethylenedioxythiophene):Polystyrenesulfonate/HfOx/Pt Memristive Structure. *Journal of Physical Chemistry C*, **2020**, 124, 4843-4851	3.8	2
137	Design of a Controllable Redox-Diffusive Threshold Switching Memristor. *Advanced Electronic Materials*, **2020**, 6, 2000695	6.4	22

136	3D Layout of Interdigital Transducers for High Frequency Surface Acoustic Wave Devices. *IEEE Access*, **2020**, 8, 123262-123271	3.5	8
135	Enhanced Performance of ZnO/SiO/AlO Surface Acoustic Wave Devices with Embedded Electrodes. *ACS Applied Materials & Interfaces*, **2020**, 12, 42378-42385	9.5	2
134	Superparaelectric (Ba0.95,Sr0.05)(Zr0.2,Ti0.8)O3 Ultracapacitors. *Advanced Energy Materials*, **2020**, 10, 2001778	21.8	24
133	Matrix Function Optimization Problems Under Orthonormal Constraint. *IEEE Transactions on Systems, Man, and Cybernetics: Systems*, **2020**, 50, 802-814	7.3	3
132	Photo-patterned oxygen sensing films based on Pt porphyrin for controlling cell growth and studying metabolism.. *RSC Advances*, **2019**, 9, 924-930	3.7	4
131	Modulating metallic conductive filaments via bilayer oxides in resistive switching memory. *Applied Physics Letters*, **2019**, 114, 193502	3.4	25
130	Emulation of Learning and Memory Behaviors by Memristor Based on Ag Migration on 2D MoS2 Surface. *Physica Status Solidi (A) Applications and Materials Science*, **2019**, 216, 1900104	1.6	22
129	Nonvolatile Memory: Performance-Enhancing Selector via Symmetrical Multilayer Design (Adv. Funct. Mater. 13/2019). *Advanced Functional Materials*, **2019**, 29, 1970081	15.6	3
128	High-frequency V-doped ZnO/SiC surface acoustic wave devices with enhanced electromechanical coupling coefficient. *Applied Physics Letters*, **2019**, 114, 113504	3.4	16
127	Phase-change nanoclusters embedded in a memristor for simulating synaptic learning. *Nanoscale*, **2019**, 11, 5684-5692	7.7	17
126	Self-Modulating Interfacial Cation Migration Induced Threshold Switching in Bilayer Oxide Memristive Device. *Journal of Physical Chemistry C*, **2019**, 123, 878-885	3.8	7
125	Simulation of temperature compensated waveguiding layer acoustic wave devices. *Journal Physics D: Applied Physics*, **2019**, 52, 075105	3	5
124	High-Frequency Surface Acoustic Wave Devices Based on ZnO/SiC Layered Structure. *IEEE Electron Device Letters*, **2019**, 40, 103-106	4.4	20
123	Performance-Enhancing Selector via Symmetrical Multilayer Design. *Advanced Functional Materials*, **2019**, 29, 1808376	15.6	38
122	Behavior of Al/Cu/Ti electrodes in surface acoustic wave filter at high power. *Current Applied Physics*, **2019**, 19, 363-369	2.6	3
121	Enhanced power durability of surface acoustic wave filter with Al/Ti/Cu/Ti electrodes. *Journal of Alloys and Compounds*, **2018**, 740, 222-228	5.7	6
120	Competition between Metallic and Vacancy Defect Conductive Filaments in a CH3NH3PbI3-Based Memory Device. *Journal of Physical Chemistry C*, **2018**, 122, 6431-6436	3.8	69
119	A Green Route to a Low Cost Anisotropic MoS2/Poly(Vinylidene Fluoride) Nanocomposite with Ultrahigh Electroactive Phase and Improved Electrical and Mechanical Properties. *ACS Sustainable Chemistry and Engineering*, **2018**, 6, 5043-5052	8.3	28

118	Texture-enhanced Al-Cu electrodes on ultrathin Ti buffer layers for high-power durable 2.6 GHz SAW filters. *AIP Advances*, **2018**, 8, 045212	1.5	8
117	Modulation of Response Patterns by Loading-Rate-Dependent Interface Polarization and Doping. *Journal of Physical Chemistry C*, **2018**, 122, 981-988	3.8	1
116	Improving Unipolar Resistive Switching Uniformity with Cone-Shaped Conducting Filaments and Its Logic-In-Memory Application. *ACS Applied Materials & Interfaces*, **2018**, 10, 6453-6462	9.5	52
115	Enhanced SAW characteristics of a-plane AlN epitaxial films using ZnO buffer layer. *Journal of Materials Science: Materials in Electronics*, **2018**, 29, 3912-3919	2.1	9
114	Characteristics of one-port surface acoustic wave resonator fabricated on ZnO/6H-SiC layered structure. *Journal Physics D: Applied Physics*, **2018**, 51, 145305	3	6
113	Improved resistance to electromigration and acoustomigration of Al interdigital transducers by Ni underlayer. *Rare Metals*, **2018**, 37, 823-830	5.5	7
112	Hydrogel-Based Fluorescent Dual pH and Oxygen Sensors Loaded in 96-Well Plates for High-Throughput Cell Metabolism Studies. *Sensors*, **2018**, 18,	3.8	21
111	Towards the minimum-cost control of target nodes in directed networks with linear dynamics. *Journal of the Franklin Institute*, **2018**, 355, 8141-8157	4	3
110	Adaptive Crystallite Kinetics in Homogenous Bilayer Oxide Memristor for Emulating Diverse Synaptic Plasticity. *Advanced Functional Materials*, **2018**, 28, 1706927	15.6	90
109	Quality-enhanced AlN epitaxial films grown on c-sapphire using ZnO buffer layer for SAW applications. *Applied Surface Science*, **2017**, 402, 392-399	6.7	27
108	Pulse Responses of the Conducting Polymer Poly(3,4-ethylenedioxythiophene): Poly(styrenesulfonate)-Based Junctions. *Journal of Electronic Materials*, **2017**, 46, 1849-1854	1.9	1
107	Diverse Synaptic Plasticity Induced by the Interplay of Ionic Polarization and Doping at Salt-Doped Electrolyte/Semiconducting Polymer Interface. *ACS Omega*, **2017**, 2, 746-754	3.9	5
106	Sputtering power dependence of structure and photoluminescence of ZnO on 6H-SiC. *Journal of Materials Science: Materials in Electronics*, **2017**, 28, 17881-17888	2.1	3
105	Guiding the Growth of a Conductive Filament by Nanoindentation To Improve Resistive Switching. *ACS Applied Materials & Interfaces*, **2017**, 9, 34064-34070	9.5	85
104	Ionic Species-Modulated Interfacial Polarization and Frequency Selectivity in Polymer Electrolyte/Semiconductor Heterojunctions. *Journal of Physical Chemistry C*, **2017**, 121, 16629-16636	3.8	1
103	Spatial summation of the short-term plasticity of a pair of organic heterogeneous junctions. *RSC Advances*, **2017**, 7, 4017-4023	3.7	5
102	Thresholds of frequency selectivity of Pt/poly(3-hexylthiophene-2,5-diyl)/polyethylene oxide + Mg2 +/Pt heterojunctions. *Solid State Ionics*, **2016**, 287, 42-47	3.3	4
101	Growth and Characterization of Polyimide-Supported AlN Films for Flexible Surface Acoustic Wave Devices. *Journal of Electronic Materials*, **2016**, 45, 2702-2709	1.9	6

100	Hierarchical Chunking of Sequential Memory on Neuromorphic Architecture with Reduced Synaptic Plasticity. *Frontiers in Computational Neuroscience*, **2016**, 10, 136	3.5	4
99	Structural and electrical properties of high Curie temperature Aurivillius phase composite ceramics with largely enhanced piezoelectricity. *Science China Technological Sciences*, **2016**, 59, 1048-1053	3.5	4
98	Simulation of pulse responses of lithium salt-doped poly ethyleneoxide. *Journal of Polymer Science, Part B: Polymer Physics*, **2016**, 54, 831-837	2.6	6
97	Manipulation of Electric Field Effect by Orbital Switch. *Advanced Functional Materials*, **2016**, 26, 753-759	15.6	40
96	Sliding threshold of spike-rate dependent plasticity of a semiconducting polymer/electrolyte cell. *Journal of Polymer Science, Part B: Polymer Physics*, **2016**, 54, 2412-2417	2.6	2
95	Simulation of synaptic short-term plasticity using Ba(CF3SO3)2-doped polyethylene oxide electrolyte film. *Scientific Reports*, **2016**, 6, 18915	4.9	12
94	Unipolar resistive switching with forming-free and self-rectifying effects in Cu/HfO2/n-Si devices. *AIP Advances*, **2016**, 6, 025007	1.5	16
93	Forming-free and self-rectifying resistive switching of the simple Pt/TaOx/n-Si structure for access device-free high-density memory application. *Nanoscale*, **2015**, 7, 6031-8	7.7	88
92	Frequency-dependent learning achieved using semiconducting polymer/electrolyte composite cells. *Nanoscale*, **2015**, 7, 16880-9	7.7	25
91	Tuning the switching behavior of binary oxide-based resistive memory devices by inserting an ultra-thin chemically active metal nanolayer: a case study on the Ta2O5-Ta system. *Physical Chemistry Chemical Physics*, **2015**, 17, 12849-56	3.6	46
90	Magnetism modulation in Cu-doped AlN via coupling between AlN thin film and ferroelectric substrate. *Journal of Alloys and Compounds*, **2015**, 618, 236-239	5.7	3
89	Development of a neuromorphic computing system **2015**,		15
88	Implementation of Complete Boolean Logic Functions in Single Complementary Resistive Switch. *Scientific Reports*, **2015**, 5, 15467	4.9	68
87	Electrical Manipulation of Orbital Occupancy and Magnetic Anisotropy in Manganites. *Advanced Functional Materials*, **2015**, 25, 864-870	15.6	84
86	Magnetoelectric Coupling Induced by Interfacial Orbital Reconstruction. *Advanced Materials*, **2015**, 27, 6651-6	24	69
85	Electrical control of the exchange spring in antiferromagnetic metals. *Advanced Materials*, **2015**, 27, 3196-201	24	80
84	Effect of heavy-ion on frequency selectivity of semiconducting polymer/electrolyte heterojunction. *RSC Advances*, **2015**, 5, 98110-98117	3.7	5
83	Controlling Ion Conductance and Channels to Achieve Synaptic-like Frequency Selectivity. *Nano-Micro Letters*, **2015**, 7, 121-126	19.5	12

82	Learning processes modulated by the interface effects in a Ti/conducting polymer/Ti resistive switching cell. *RSC Advances*, **2014**, 4, 14822	3.7	45
81	Anti-Ferromagnet Controlled Tunneling Magnetoresistance. *Advanced Functional Materials*, **2014**, 24, 6806-6810	15.6	27
80	Recent progress in resistive random access memories: Materials, switching mechanisms, and performance. *Materials Science and Engineering Reports*, **2014**, 83, 1-59	30.9	950
79	Reversible Ferromagnetic Phase Transition in Electrode-Gated Manganites. *Advanced Functional Materials*, **2014**, 24, 7233-7240	15.6	63
78	Tuning the entanglement between orbital reconstruction and charge transfer at a film surface. *Scientific Reports*, **2014**, 4, 4206	4.9	41
77	Ferroelectric polymer nanostructures: fabrication, structural characteristics and performance under confinement. *Journal of Nanoscience and Nanotechnology*, **2014**, 14, 2086-100	1.3	31
76	Resistive switching and conductance quantization in Ag/SiO2/indium tin oxide resistive memories. *Applied Physics Letters*, **2014**, 105, 063504	3.4	71
75	Frequency selectivity in pulse responses of Pt/poly(3-hexylthiophene-2,5-diyl)/polyethylene oxide +Li+/Pt hetero-junction. *PLoS ONE*, **2014**, 9, e108316	3.7	19
74	Enhancement of room temperature ferromagnetism in Cu-doped AlN thin film by defect engineering. *Journal of Alloys and Compounds*, **2014**, 586, 469-474	5.7	20
73	Resistive switching with self-rectifying behavior in Cu/SiOx/Si structure fabricated by plasma-oxidation. *Journal of Applied Physics*, **2013**, 113, 244502	2.5	28
72	Synaptic plasticity and learning behaviours mimicked through Ag interface movement in an Ag/conducting polymer/Ta memristive system. *Journal of Materials Chemistry C*, **2013**, 1, 5292	7.1	185
71	Significant enhancement in electromigration resistance and texture of aluminum films using an ultrathin titanium underlayer. *Acta Materialia*, **2013**, 61, 4619-4624	8.4	7
70	Conductance quantization in a Ag filament-based polymer resistive memory. *Nanotechnology*, **2013**, 24, 335201	3.4	71
69	Formation process of conducting filament in planar organic resistive memory. *Applied Physics Letters*, **2013**, 102, 141606	3.4	74
68	Enhancement of piezoelectric response of diluted Ta doped AlN. *Applied Surface Science*, **2013**, 270, 225-230	2.7	32
67	Correlation of oxygen vacancy variations to band gap changes in epitaxial ZnO thin films. *Applied Physics Letters*, **2013**, 102, 181908	3.4	91
66	Reply to "Comment on "Dynamic Processes of Resistive Switching in Metallic Filament-Based Organic Memory Devices"" *Journal of Physical Chemistry C*, **2013**, 117, 11881-11882	3.8	11
65	Programmable complementary resistive switching behaviours of a plasma-oxidised titanium oxide nanolayer. *Nanoscale*, **2013**, 5, 422-8	7.7	60

64	Influence of sputtering parameters on structures and residual stress of AlN films deposited by DC reactive magnetron sputtering at room temperature. *Journal of Crystal Growth*, **2013**, 363, 80-85	1.6	60
63	A new type of glucose biosensor based on surface acoustic wave resonator using Mn-doped ZnO multilayer structure. *Biosensors and Bioelectronics*, **2013**, 49, 512-8	11.8	75
62	Insensitivity of tunneling anisotropic magnetoresistance to non-magnetic electrodes. *Applied Physics Letters*, **2013**, 103, 202403	3.4	6
61	Interplay between chemical state, electric properties, and ferromagnetism in Fe-doped ZnO films. *Journal of Applied Physics*, **2013**, 113, 104503	2.5	27
60	In situ observation of the nanocrystal growth and their piezoelectric performance change in P(VDF-TrFE) films by hot stage piezoresponse force microscopy. *Journal of Applied Physics*, **2013**, 113, 187210	2.5	8
59	Resistive switching behaviour of a tantalum oxide nanolayer fabricated by plasma oxidation. *Physica Status Solidi - Rapid Research Letters*, **2013**, 7, 282-284	2.5	15
58	Growth of epitaxial c -plane ZnO film on a -plane sapphire by radio frequency reactive magnetron sputtering. *Physica Status Solidi - Rapid Research Letters*, **2013**, 7, 587-589	2.5	3
57	Giant piezoresponse and promising application of environmental friendly small-ion-doped ZnO. *Science China Technological Sciences*, **2012**, 55, 421-436	3.5	20
56	Effects of Mn-doping on surface acoustic wave properties of ZnO films. *Physica Status Solidi - Rapid Research Letters*, **2012**, 6, 436-438	2.5	11
55	Structure and ferromagnetism in vanadium-doped LiNbO3. *Journal of Applied Physics*, **2012**, 112, 033913	2.5	7
54	Resistive switching induced by metallic filaments formation through poly(3,4-ethylene-dioxythiophene):poly(styrenesulfonate). *ACS Applied Materials & Interfaces*, **2012**, 4, 447-53	9.5	87
53	Dynamic Processes of Resistive Switching in Metallic Filament-Based Organic Memory Devices. *Journal of Physical Chemistry C*, **2012**, 116, 17955-17959	3.8	175
52	Resistive switching and magnetic modulation in cobalt-doped ZnO. *Advanced Materials*, **2012**, 24, 3515-20	14	234
51	Bipolar resistive switching with self-rectifying effects in Al/ZnO/Si structure. *Journal of Applied Physics*, **2012**, 111, 013702	2.5	93
50	Oxygen migration induced resistive switching effect and its thermal stability in W/TaOx/Pt structure. *Applied Physics Letters*, **2012**, 100, 253509	3.4	87
49	Effect of carbon doping on microstructure, electronic and magnetic properties of Cr:AlN films. *Journal of Alloys and Compounds*, **2011**, 509, 440-446	5.7	8
48	Strong d□ electron interaction inducing ferromagnetism in Mn-doped LiNbO3. *Thin Solid Films*, **2011**, 520, 764-768	2.2	8
47	Modulating resistive switching by diluted additive of poly(vinylpyrrolidone) in poly(3,4-ethylenedioxythiophene):poly(styrenesulfonate). *Journal of Applied Physics*, **2011**, 110, 114518	2.5	15

46	Response to Comment on Enhanced spin injection and voltage bias in (Zn,Co)O/MgO/(Zn,Co)O magnetic tunnel junctions [Appl. Phys. Lett. 96, 116101 (2010)]. *Applied Physics Letters*, **2010**, 96, 116102	3.4	
45	Reproducible and controllable organic resistive memory based on Al/poly(3,4-ethylene-dioxythiophene):poly(styrenesulfonate)/Al structure. *Applied Physics Letters*, **2010**, 97, 253301	3.4	45
44	Bipolar resistive switching in Cu/AlN/Pt nonvolatile memory device. *Applied Physics Letters*, **2010**, 97, 083502	3.4	117
43	Hysteretic giant magnetoresistance curves induced by interlayer magnetostatic coupling in [Pd/Co]/Cu/Co/Cu/[Co/Pd] dual spin valves. *Journal of Applied Physics*, **2010**, 107, 083902	2.5	8
42	Multilevel resistance switching in Cu/TaOx/Pt structures induced by a coupled mechanism. *Journal of Applied Physics*, **2010**, 107, 093701	2.5	37
41	Enhanced electromechanical response of Fe-doped ZnO films by modulating the chemical state and ionic size of the Fe dopant. *Physical Review B*, **2010**, 82,	3.3	76
40	Metastable structure and magnetism of Cr-doped AlN in AlN/TiN multilayers. *Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics*, **2010**, 28, 62-65	1.3	5
39	Influence of the Mn concentration on the electromechanical response d33 of Mn-doped ZnO films. *Physica Status Solidi - Rapid Research Letters*, **2010**, 4, 209-211	2.5	8
38	Filtering performance improvement in V-doped ZnO/diamond surface acoustic wave filters. *Applied Surface Science*, **2010**, 256, 3081-3085	6.7	35
37	Nonvolatile resistive switching memories-characteristics, mechanisms and challenges. *Progress in Natural Science: Materials International*, **2010**, 20, 1-15	3.6	151
36	Influence of strain and grain boundary variations on magnetism of Cr-doped AlN films. *Journal of Applied Physics*, **2009**, 106, 073907	2.5	9
35	Switching mechanism transition induced by annealing treatment in nonvolatile Cu/ZnO/Cu/ZnO/Pt resistive memory: From carrier trapping/detrapping to electrochemical metallization. *Journal of Applied Physics*, **2009**, 106, 123705	2.5	64
34	Oxygen vacancy effect on room-temperature ferromagnetism of rutile Co:TiO2 thin films. *Applied Physics Letters*, **2009**, 94, 042508	3.4	51
33	Influence of Cr-doping on microstructure and piezoelectric response of AlN films. *Journal Physics D: Applied Physics*, **2009**, 42, 235406	3	31
32	Enhanced spin injection and voltage bias in (Zn,Co)O/MgO/(Zn,Co)O magnetic tunnel junctions. *Applied Physics Letters*, **2009**, 95, 232508	3.4	15
31	Room Temperature Ferromagnetism in Cobalt-Doped LiNbO3 Single Crystalline Films. *Crystal Growth and Design*, **2009**, 9, 1235-1239	3.5	14
30	Tensile properties of Cr inserted amorphous Co85Zr9Nb6 films deposited on polymer substrate. *Journal of Alloys and Compounds*, **2009**, 477, 239-242	5.7	3
29	Grain boundary defects-mediated room temperature ferromagnetism in Co-doped ZnO film. *Journal of Alloys and Compounds*, **2009**, 482, 224-228	5.7	21

28	Correlation between donor defects and ferromagnetism in insulating Sn1−xCoxO2 films. *Journal of Applied Physics*, **2009**, 105, 093931	2.5	2
27	Interlayer magnetostatic coupling induced Co layer coercivity enhancement and exchange bias in [Pd/Co]/Cu/Co spin valves. *Applied Physics Letters*, **2009**, 95, 172512	3.4	10
26	The role of rotatable anisotropy in the asymmetric magnetization reversal of exchange biased NiO/Ni bilayers. *Journal of Applied Physics*, **2009**, 106, 013902	2.5	24
25	Fully room-temperature-fabricated nonvolatile resistive memory for ultrafast and high-density memory application. *Nano Letters*, **2009**, 9, 1636-43	11.5	718
24	Room temperature multiferroic behavior of Cr-doped ZnO films. *Journal of Applied Physics*, **2008**, 104, 064102	2.5	57
23	Giant piezoelectric d33 coefficient in ferroelectric vanadium doped ZnO films. *Applied Physics Letters*, **2008**, 92, 012907	3.4	147
22	Room temperature ferromagnetism and ferroelectricity in cobalt-doped LiNbO3 film. *Applied Physics Letters*, **2008**, 92, 262901	3.4	21
21	Tuning the training effect in exchange biased NiO/Ni bilayers. *Applied Physics Letters*, **2008**, 92, 243113	3.4	17
20	Strain-induced ferromagnetism enhancement in Co:ZnO films. *Journal of Applied Physics*, **2008**, 103, 093911	2.5	41
19	Cr-substitution-induced ferroelectric and improved piezoelectric properties of Zn1−xCrxO films. *Journal of Applied Physics*, **2008**, 103, 074107	2.5	71
18	Ferromagnetism and possible application in spintronics of transition-metal-doped ZnO films. *Materials Science and Engineering Reports*, **2008**, 62, 1-35	30.9	570
17	Nanoindentation study of amorphous-Co79Zr13Nb8/Cr multilayers. *Surface and Coatings Technology*, **2008**, 202, 3239-3245	4.4	17
16	Amorphous phase and anisotropy induced by glancing incident ion beams in CoNb films. *Nuclear Instruments & Methods in Physics Research B*, **2008**, 266, 3545-3551	1.2	1
15	Microstructure and mechanical properties of polycrystalline-Ag/amorphous-CoZrNb multilayers. *Surface and Coatings Technology*, **2007**, 201, 7932-7938	4.4	8
14	Metastable phases in CoAg system formed by ion beam assisted deposition at the glancing ion incidence. *Nuclear Instruments & Methods in Physics Research B*, **2007**, 260, 547-552	1.2	4
13	Soft magnetic properties of amorphous-CoZr/ polycrystalline-M (M = Cu, Ag, Al, Cr) multilayers. *Applied Physics A: Materials Science and Processing*, **2007**, 90, 305-310	2.6	1
12	Enhancement of electrical and ferromagnetic properties by additional Al doping in Co:ZnO thin films. *Journal of Physics Condensed Matter*, **2007**, 19, 296208	1.8	34
11	Fully epitaxial (Zn,Co)O/ZnO/(Zn,Co)O junction and its tunnel magnetoresistance. *Applied Physics Letters*, **2007**, 91, 042106	3.4	32

10	Anomalous voltage dependence of tunnel magnetoresistance in (Zn, Co)O-based junction with double barrier. *Applied Physics Letters*, **2007**, 91, 172109	3.4	10
9	Nanoindentation investigation of the mechanical behaviors of nanoscale Ag/Cu multilayers. *Journal of Materials Research*, **2007**, 22, 3423-3431	2.5	26
8	Local Co structure and ferromagnetism in ion-implanted Co-doped LiNbO3. *Physical Review B*, **2006**, 73,	3.3	40
7	Giant magnetic moment in an anomalous ferromagnetic insulator: Co-doped ZnO. *Physical Review B* , **2006**, 73,	3.3	216
6	Magnetic Properties of Fe/Ho Multilayers Prepared by Electron-Beam Evaporation. *Journal of the Physical Society of Japan*, **2006**, 75, 084701	1.5	3
5	Skew Ion-Bombardment-Induced Microstructure and Magnetic Anisotropy Evolutions in the Immiscible Co□u System during Deposition Process. *Japanese Journal of Applied Physics*, **2003**, 42, 6869-6874	1.4	7
4	Formation of metastable alloy films in the Ni-Mo binary system by ion-beam-assisted deposition. *Applied Physics A: Materials Science and Processing*, **2003**, 77, 523-528	2.6	4
3	Microstructures of Nb□i alloy films prepared by ion beam assisted deposition. *Materials Science & Engineering A: Structural Materials: Properties, Microstructure and Processing*, **2003**, 357, 365-368	5.3	5
2	Ion beam induced growth of amorphous alloy films in the Co□b system during ion beam assisted deposition. *Journal of Alloys and Compounds*, **2002**, 335, 181-187	5.7	10
1	Poster: Electronic Structure, Lattice Dynamics, and Transport471-522		